

ABSTRACT OF THE DISCLOSURE

A nitride compound semiconductor element having improved characteristics, productivity and yield. A nitride
5 compound semiconductor element comprises: a sapphire substrate; a first single crystalline layer of AlN formed on said sapphire substrate; a second single crystalline layer formed on said first single crystalline layer, said second single crystalline layer being made of $\text{Al}_x\text{Ga}_{1-x}\text{N}$ (0.8
10 $\leq x \leq 0.97$) and having a thickness of equal to or more than $0.3 \mu\text{m}$ and equal to or less than $6 \mu\text{m}$; and a device structure section of a nitride semiconductor formed on said second single crystalline layer.